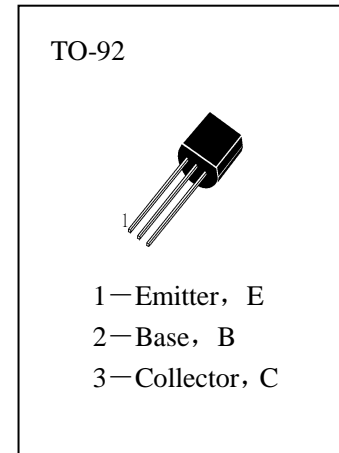


■ APPLICATIONS

The H733 is designed for driver stage of AF amplifier
And low speed switching.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation	250mW
V _{CB0}	Collector-Base Voltage	-60V
V _{CEO}	Collector-Emitter Voltage	-50V
V _{EBO}	Emitter-Base Voltage	-5V
I _C	Collector Current	-150mA



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	-60			V	I _C =-100 μA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	-50			V	I _C =-10mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	-5			V	I _E =-10 μA, I _C =0
h _{FE}	DC Current Gain	90		600		V _{CE} =-6V, I _C =-1mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			-0.3	V	I _C =-100mA, I _B =-10mA
V _{BE(ON)}	Base-Emitter On Voltage	-0.5		-0.8	V	V _{CE} =-6V, I _C =-1mA
I _{CBO}	Collector Cut-off Current			-100	nA	V _{CB} =-60V, I _E =0
I _{EBO}	Emitter Cut-off Current			-100	nA	V _{EB} =-5V, I _C =0
f _T	Current Gain-Bandwidth Product		180		MHz	V _{CE} =-6V, I _C =-10mA
C _{ob}	Output Capacitance		4.5		pF	V _{CB} =-10V, I _E =0 , f=1MHz

■ h_{FE} Classification

R	Q	P	K
90—180	135—270	200—400	300—600